

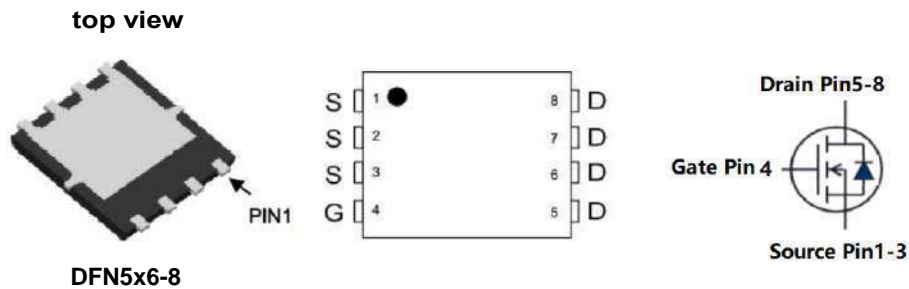
## Features

- High ruggedness
- Low Gate Charge (Typ 143nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application: Synchronous Rectification, Li Battery Protect Board, Inverter



## Product Summary

$V_{DS}$	30	V
$R_{DS(on), Typ} @ V_{GS}=10V$	1.7	mΩ
$I_D$	150	A



## Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DSS}$	Drain to source voltage	30	V
$I_D$	Continuous drain current (@ $T_c=25^\circ\text{C}$ )	150*	A
	Continuous drain current (@ $T_c=100^\circ\text{C}$ )	78*	A
$I_{DM}$	Drain current pulsed(note 1)	600	A
$I_{DSM}$	Continuous drain current (@ $T_a=25^\circ\text{C}$ )	30	A
	Continuous drain current (@ $T_a=70^\circ\text{C}$ )	24	A
$V_{GS}$	Gate to source voltage	$\pm 20$	V
$E_{AS}$	Single pulsed avalanche energy (note 2)	576	mJ
$E_{AR}$	Repetitive avalanche energy (note 1)	57	mJ
dv/dt	Peak diode recovery dv/dt (note 3)	5	V/ns
$P_D$	Total power dissipation (@ $T_c=25^\circ\text{C}$ )	43	W
	Total power dissipation (@ $T_a=25^\circ\text{C}$ )	2.6	W
$T_{STG}, T_J$	Operating junction temperature & storage temperature	-55 ~ + 150	$^\circ\text{C}$

\*. Drain current is limited by junction temperature.

## Thermal characteristics

Symbol	Parameter	Value	Unit
$R_{thjc}$	Thermal resistance, Junction to case	1.8	$^\circ\text{C}/\text{W}$
$R_{thja}$	Thermal resistance, Junction to ambient	62	$^\circ\text{C}/\text{W}$

Note:  $R_{thja}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{thjc}$  is guaranteed by design while  $R_{thca}$  is determined by the user's board design.

**Electrical characteristic ( T<sub>J</sub> = 25°C unless otherwise specified )**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
BV <sub>DSS</sub>	Drain to source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown voltage temperature coefficient	I <sub>D</sub> =250uA, referenced to 25°C		0.02		V/°C
I <sub>DSS</sub>	Drain to source leakage current	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =24V, T <sub>J</sub> =125°C			50	uA
I <sub>GSS</sub>	Gate to source leakage current, forward	V <sub>GS</sub> =20V, V <sub>DS</sub> =0V			100	nA
	Gate to source leakage current, reverse	V <sub>GS</sub> =-20V, V <sub>DS</sub> =0V			-100	nA
<b>On characteristics</b>						
V <sub>GS(TH)</sub>	Gate threshold voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1.2		2.4	V
R <sub>DS(ON)</sub>	Drain to source on state resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =30A, T <sub>J</sub> =25°C		3.4	4.5	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =30A, T <sub>J</sub> =25°C		1.7	2.5	mΩ
G <sub>fs</sub>	Forward transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A		73		S
<b>Dynamic characteristics</b>						
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =15V, f=1MHz		6272		pF
C <sub>oss</sub>	Output capacitance			1022		
C <sub>riss</sub>	Reverse transfer capacitance			718		
t <sub>d(on)</sub>	Turn on delay time	V <sub>DS</sub> =15V, I <sub>D</sub> =30A, R <sub>G</sub> =4.7Ω, V <sub>GS</sub> =10V (note 4,5)		20		ns
t <sub>r</sub>	Rising time			58		
t <sub>d(off)</sub>	Turn off delay time			158		
t <sub>f</sub>	Fall time			77		
Q <sub>g</sub>	Total gate charge	V <sub>DS</sub> =24V, V <sub>GS</sub> =10V, I <sub>D</sub> =30A, I <sub>G</sub> =5mA (note 4,5)		143		nC
Q <sub>gs</sub>	Gate-source charge			17		
Q <sub>gd</sub>	Gate-drain charge			43		
R <sub>g</sub>	Gate resistance	V <sub>DS</sub> =0V, Scan F mode		4.2		Ω

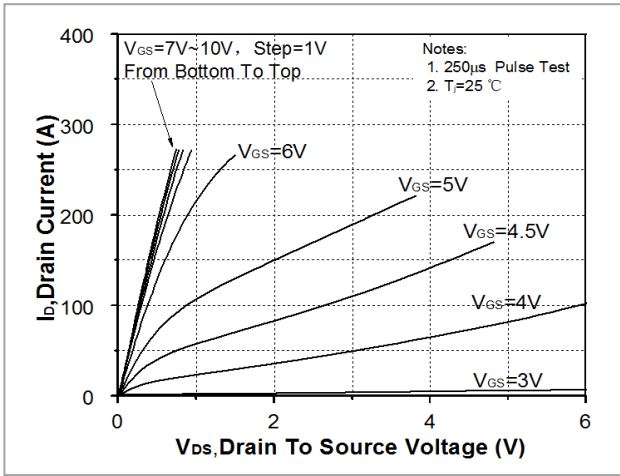
**Source to drain diode ratings characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			150	A
I <sub>SM</sub>	Pulsed source current				600	A
V <sub>SD</sub>	Diode forward voltage drop.	I <sub>S</sub> =45A, V <sub>GS</sub> =0V			1.4	V
t <sub>rr</sub>	Reverse recovery time	I <sub>S</sub> =30A, V <sub>GS</sub> =0V,		26		ns
Q <sub>rr</sub>	Reverse recovery charge	dI <sub>F</sub> /dt=100A/us		10		nC

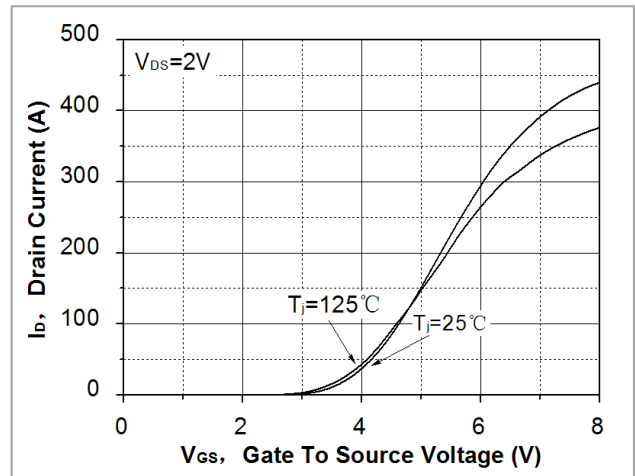
**※. Notes**

1. Repeattive rating : pulse width limited by junction temperature.
2. L =0.5mH, I<sub>AS</sub> =48A, V<sub>DD</sub>=30V, R<sub>G</sub>=25Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤30A, di/dt = 100A/us, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> =25°C
4. Pulse Test : Pulse Width ≤ 300us, duty cycle ≤ 2%.
5. Essentially independent of operating temperature.

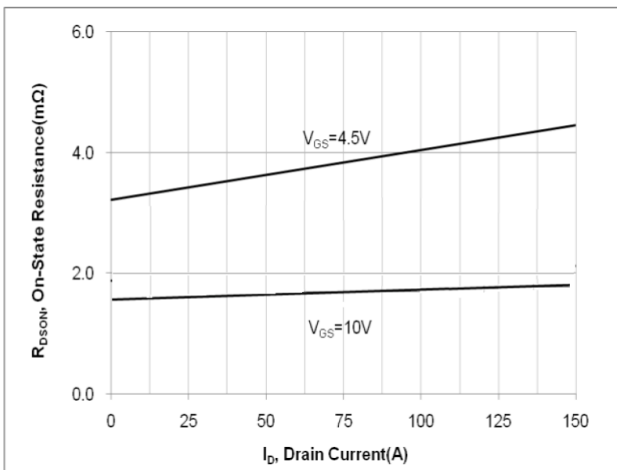
**Fig. 1. On-state characteristics**



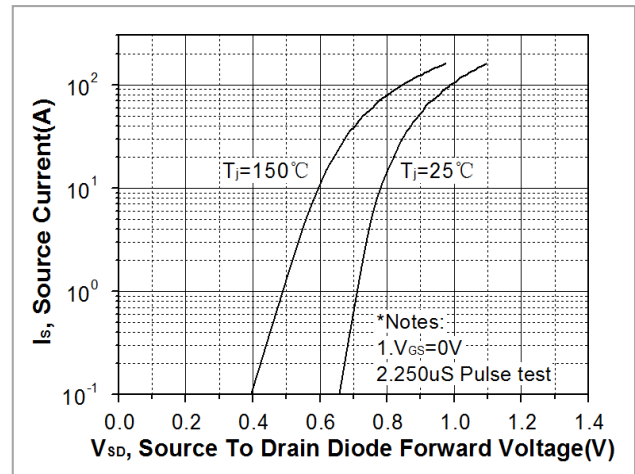
**Fig. 2. Transfer Characteristics**



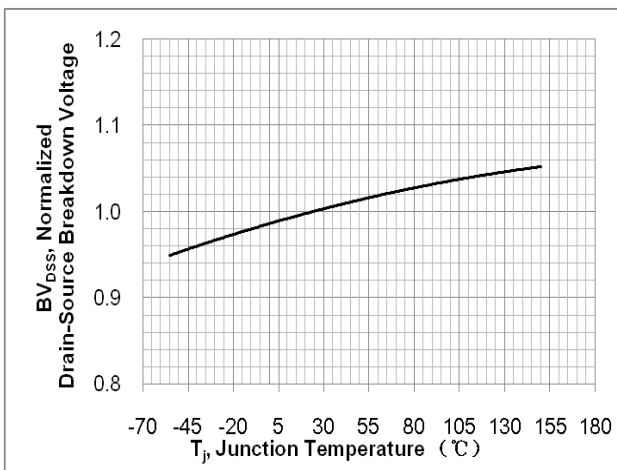
**Fig. 3. On-resistance variation vs. drain current and gate voltage**



**Fig. 4. On-state current vs. diode forward voltage**



**Fig 5. Breakdown voltage variation vs. junction temperature**



**Fig. 6. On-resistance variation vs. junction temperature**

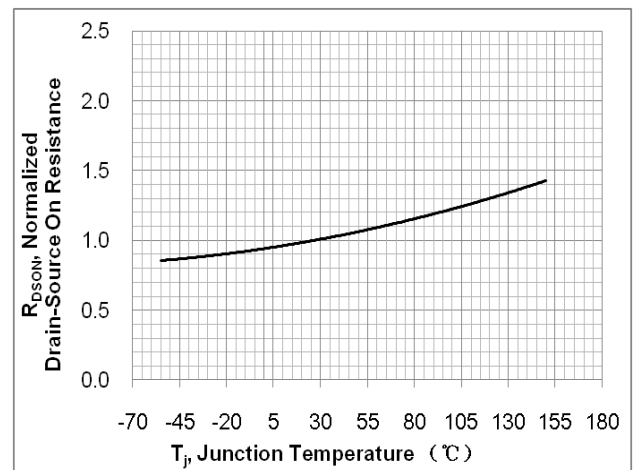


Fig. 7. Gate charge characteristics

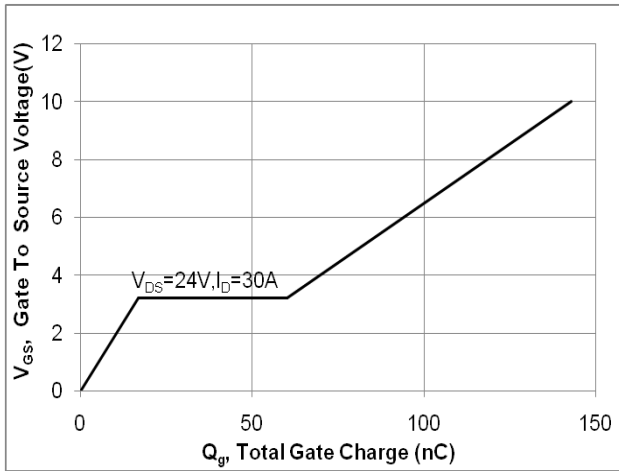


Fig. 8. Capacitance Characteristics

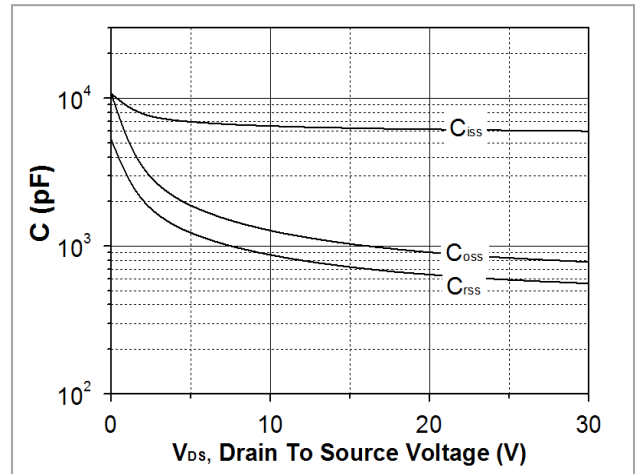


Fig. 9. Maximum safe operating area

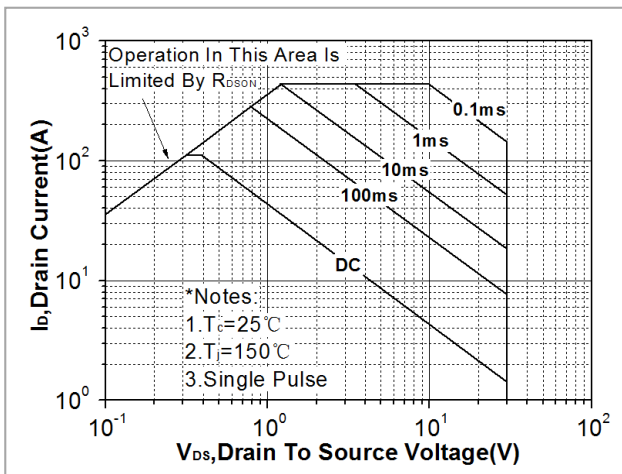


Fig. 10. Maximum drain current vs. case temperature

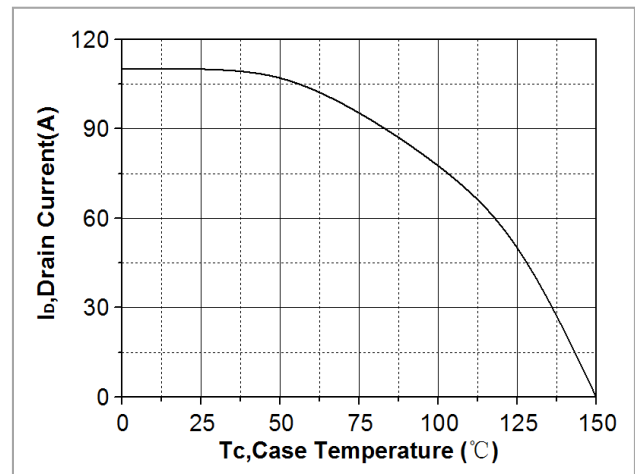


Fig. 11. Transient thermal response curve

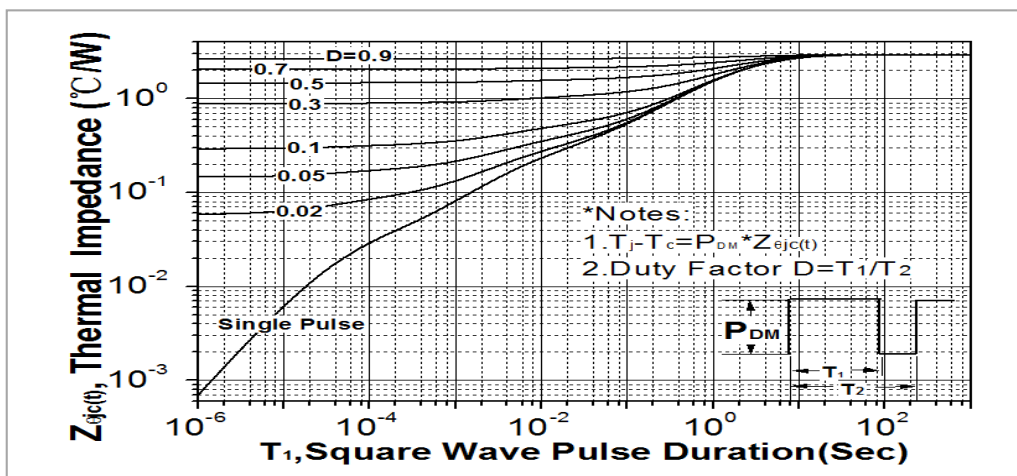


Fig. 12. Gate charge test circuit & waveform

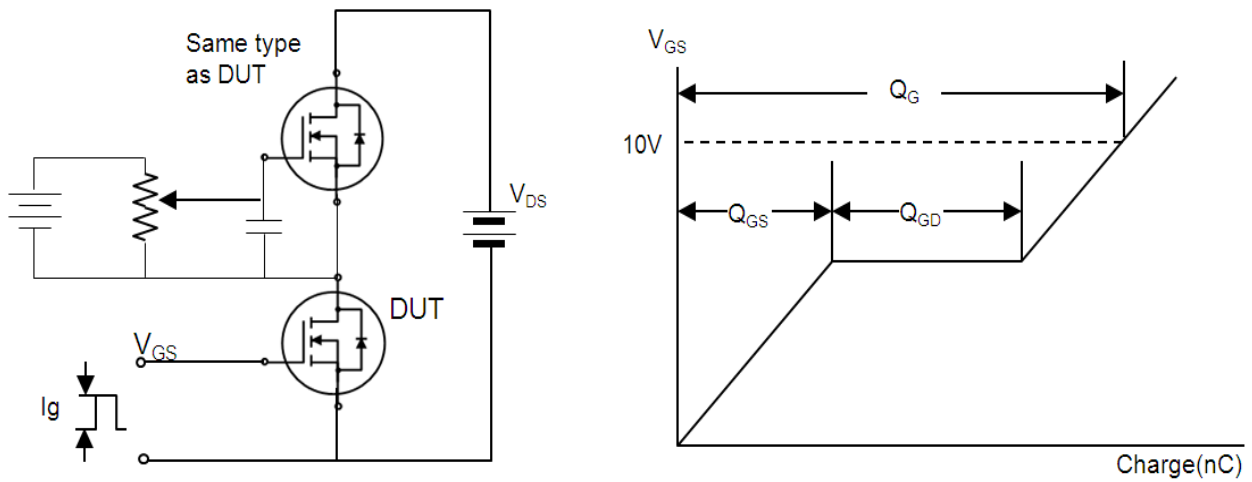


Fig. 13. Switching time test circuit & waveform

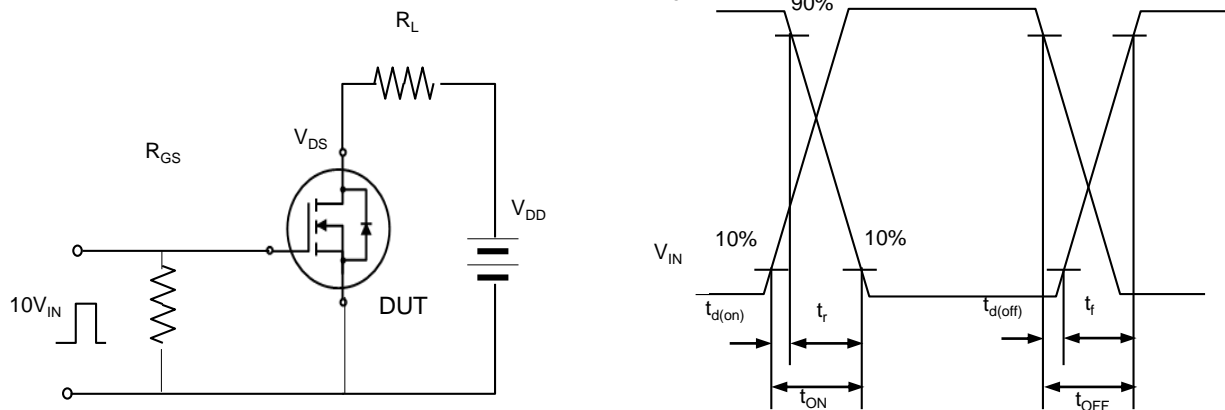


Fig. 14. Unclamped Inductive switching test circuit & waveform

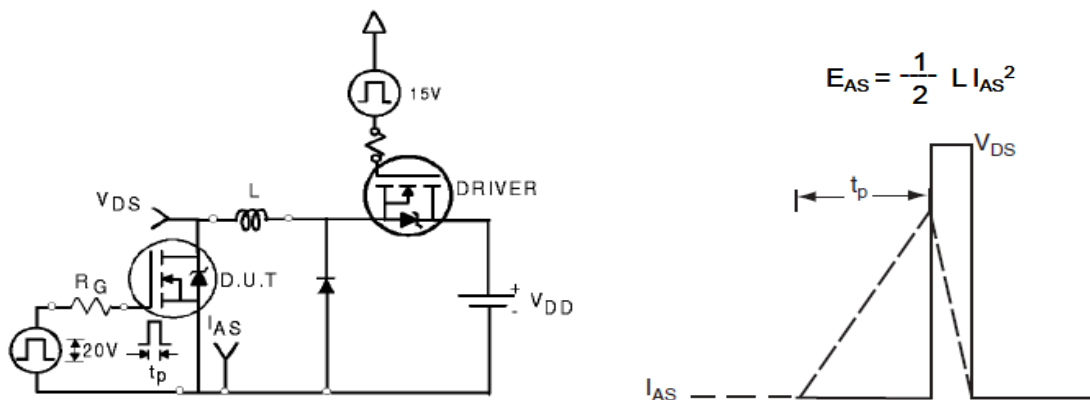
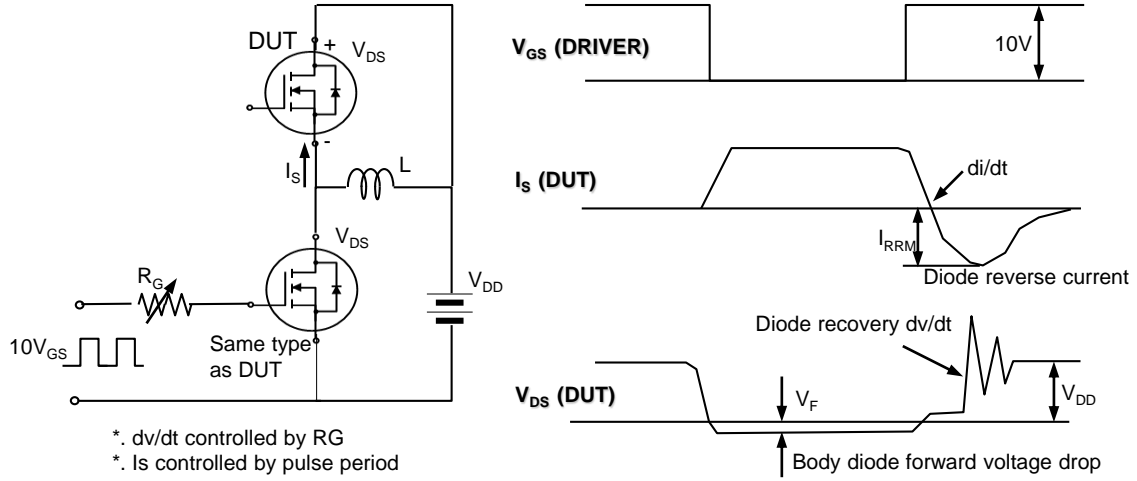
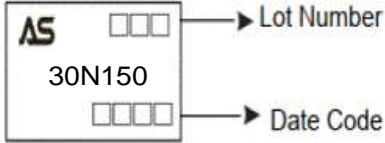


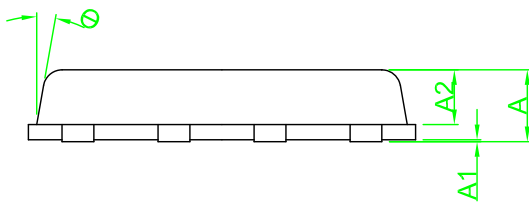
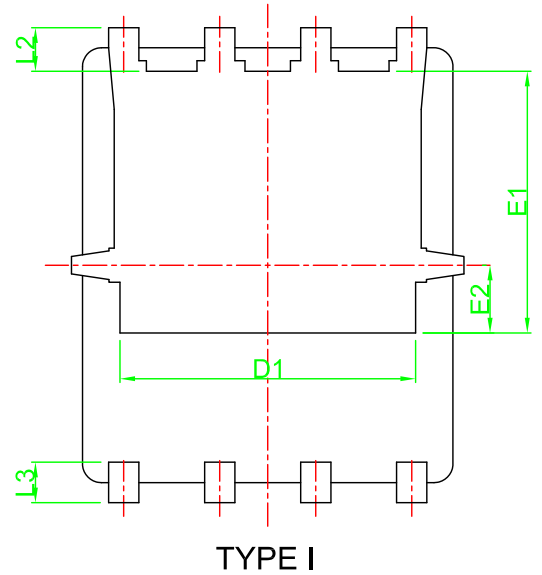
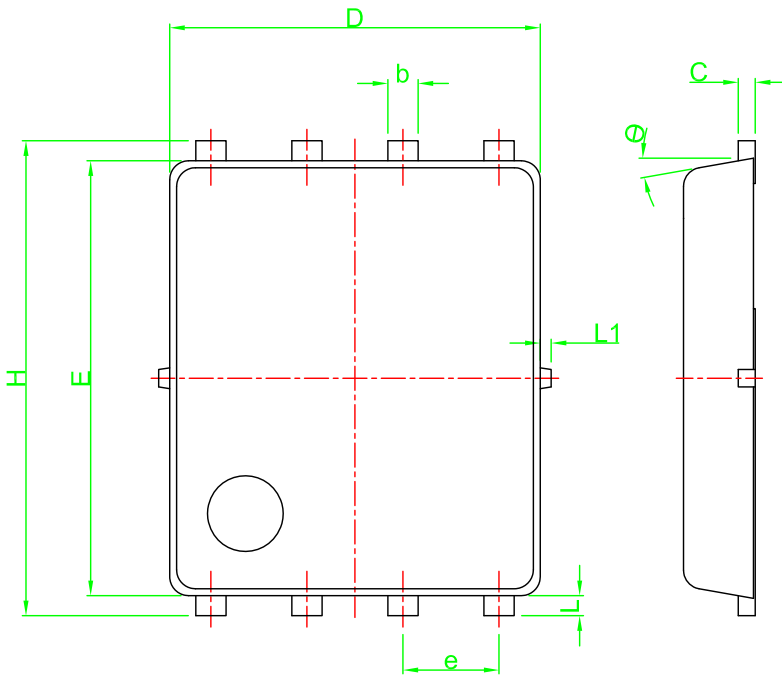
Fig. 15. Peak diode recovery dv/dt test circuit & waveform



## Ordering and Marking Information

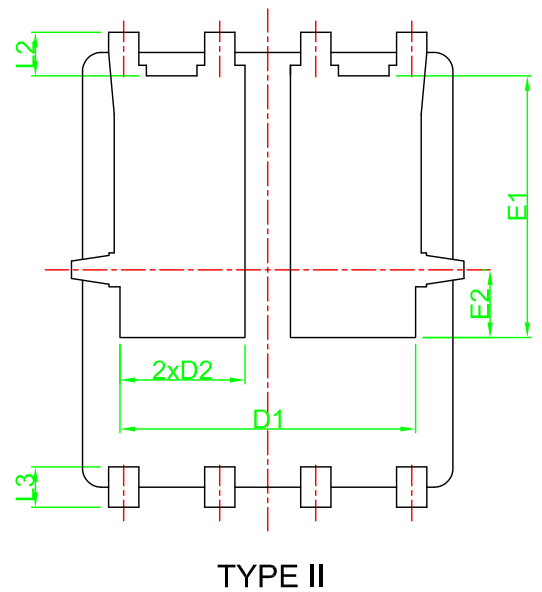
Ordering Device No.	Marking	Package	Packing	Quantity
ASDM30N150Q-R	30N150	DFN5*6-8	Tape&Reel	4000/ Reel

PACKAGE	MARKING
DFN5*6-8	 <p>AS    □□□ → Lot Number 30N150 □□□□ → Date Code</p>



DFN5\*6-8

Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	0.85	1.00	0.033	0.039
A1	0.01	0.05	0.000	0.002
A2	0.69	0.75	0.027	0.030
b	0.40	0.45	0.016	0.018
C	0.20	0.30	0.008	0.012
D	4.80	4.95	0.189	0.195
D1	3.91	4.06	0.154	0.160
D2	1.60	1.80	0.063	0.071
e	1.27 TYP		0.05 TYP	
E	5.65	5.80	0.222	0.228
E1	3.46	3.50	0.136	0.138
E2	0.80	0.95	0.031	0.037
L	0.15	0.3	0.006	0.012
L1	0.08	0.15	0.003	0.006
L2	0.58	0.73	0.023	0.029
L3	0.45	0.60	0.018	0.024
H	6.15	6.28	0.242	0.247
theta	8°	12°	8°	12°





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